DMN5L06W

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

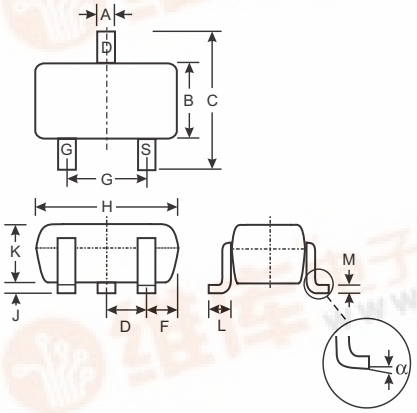
NEW PRODUCT

Features

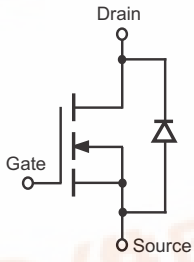
- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking: Date Code and Type Code, See Page 2
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-323		
Dim	**Min**	**Max**
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
α	0°	8°
All Dimensions in mm		



EQUIVALENT CIRCUIT

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	50	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$		V_{DGR}	50	V
Gate-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 1)	Continuous	I_D	280	mA
Drain Current (Note 1)	Pulsed	I_{DM}	1.5	A
Total Power Dissipation (Note 1)		P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)		$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range		T_j, T_{STG}	-55 to +150	°C

Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. No purposefully added lead.
3. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

NEW PRODUCT

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current @ T_C = 25°C @ T_C = 125°C	I_{DSS}	—	—	0.1 500	μA	V_{DS} = 50V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±20	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	0.49	—	1.2	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	— —	1.6 2.2	3 4	Ω	V_{GS} = 2.7V, I_D = 0.2A, V_{GS} = 1.8V, I_D = 50mA
On-State Drain Current	$I_{D(ON)}$	0.5	1.0	—	A	V_{GS} = 10V, V_{DS} = 7.5V
Forward Transconductance	$\|Y_{fs}\|$	200	—	—	mS	V_{DS} =10V, I_D = 0.2A
Source-Drain Diode Forward Voltage	V_{SD}	0.5	—	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	

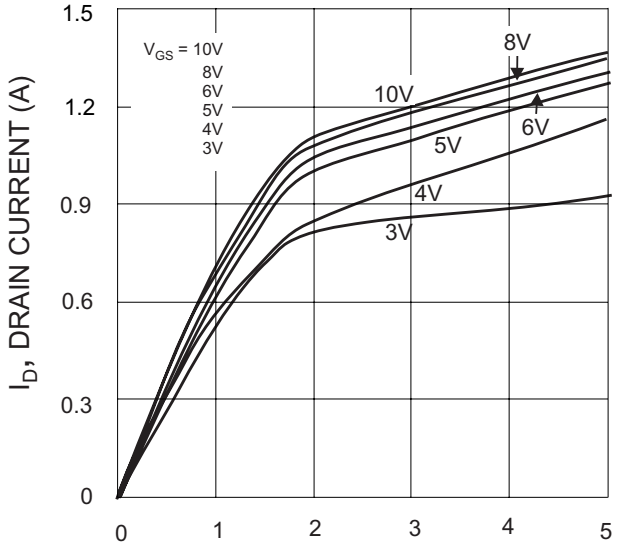


Fig. 1 Typical Output Characteristics

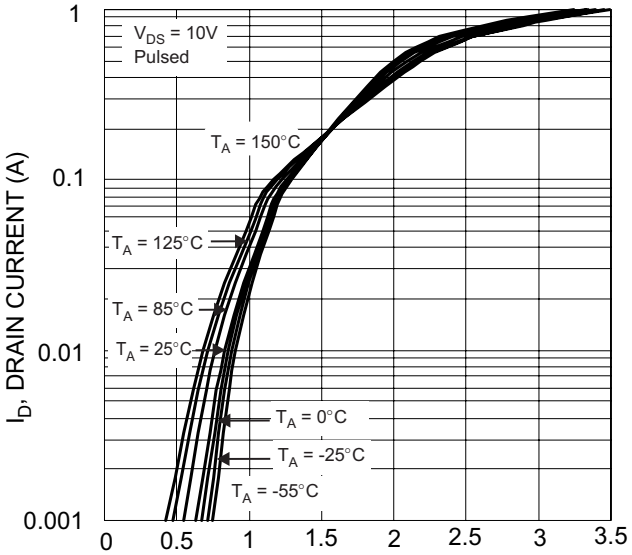


Fig. 2 Typical Transfer Characteristics

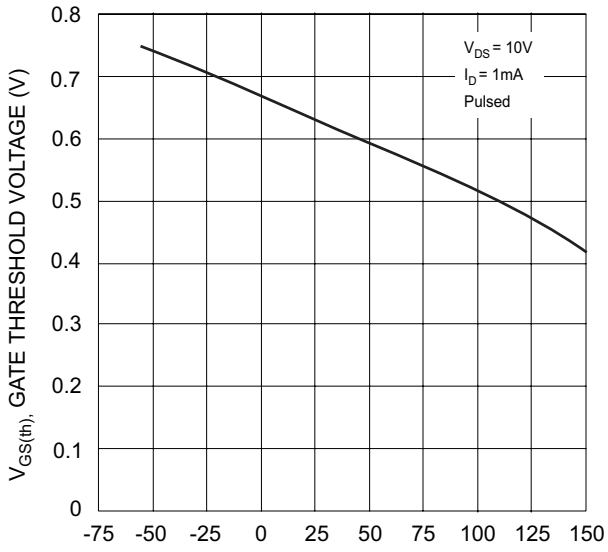


Fig. 3 Gate Threshold Voltage

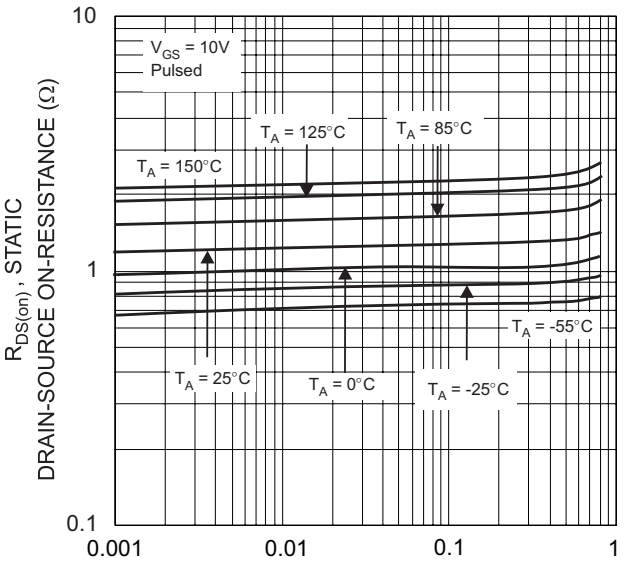


Fig. 4 Static Drain-Source On-Resistance

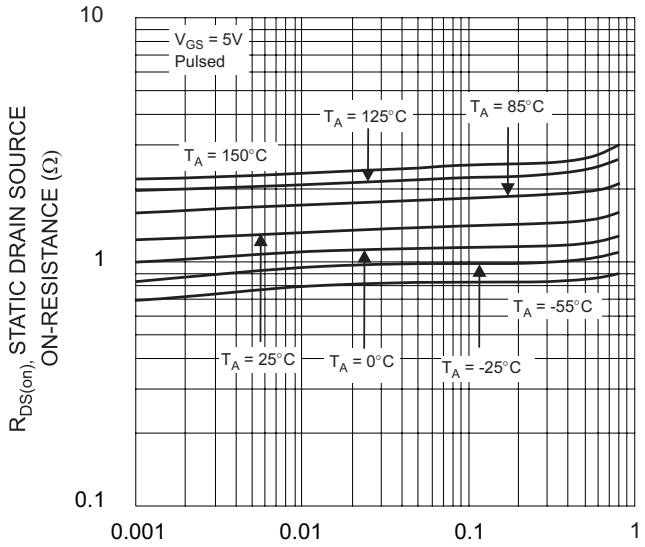


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

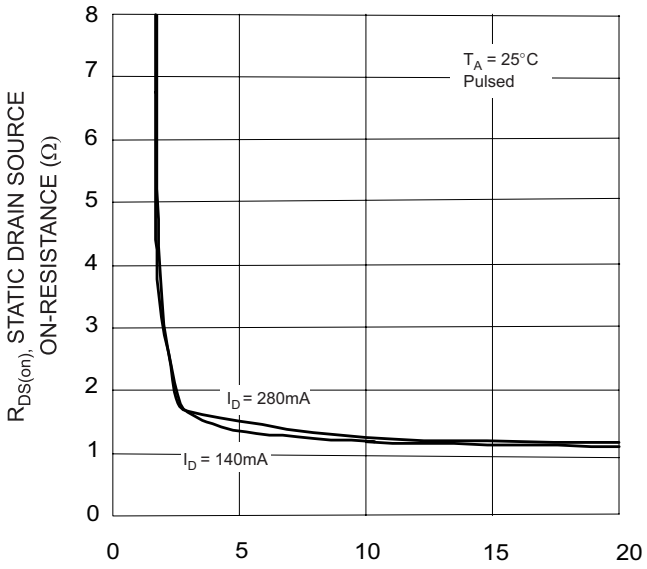


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

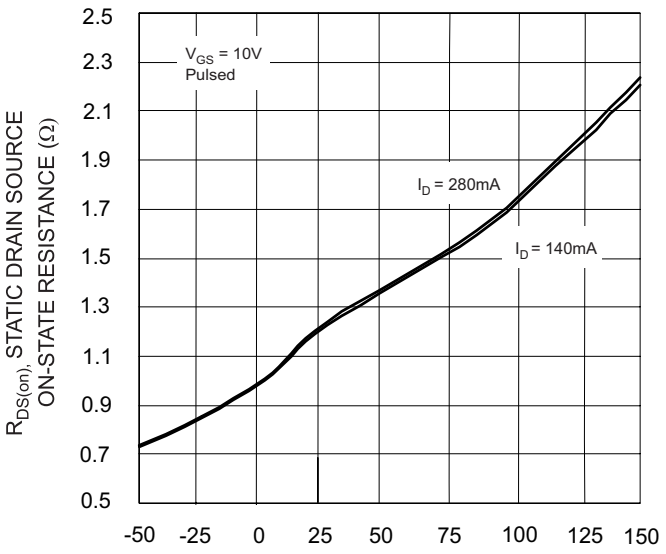


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

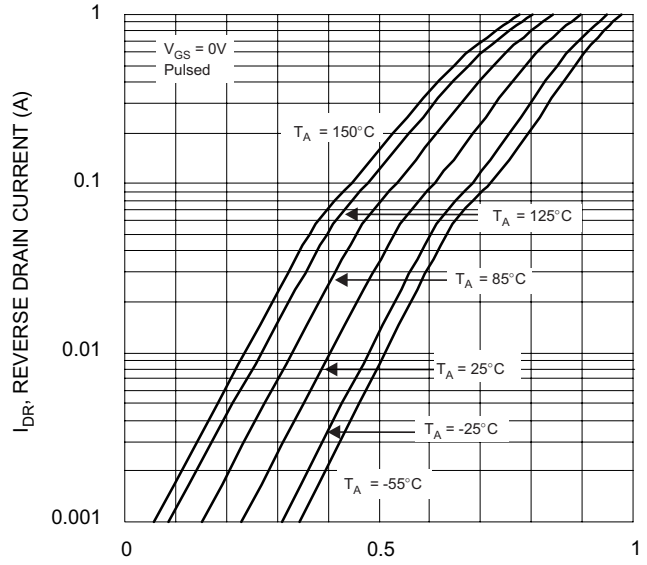


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

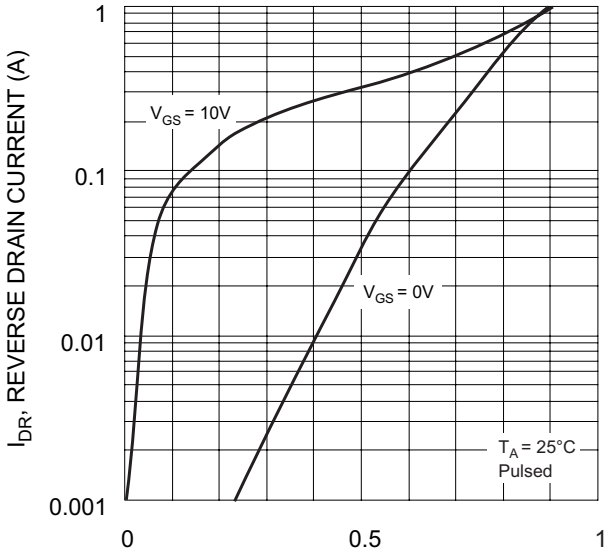


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

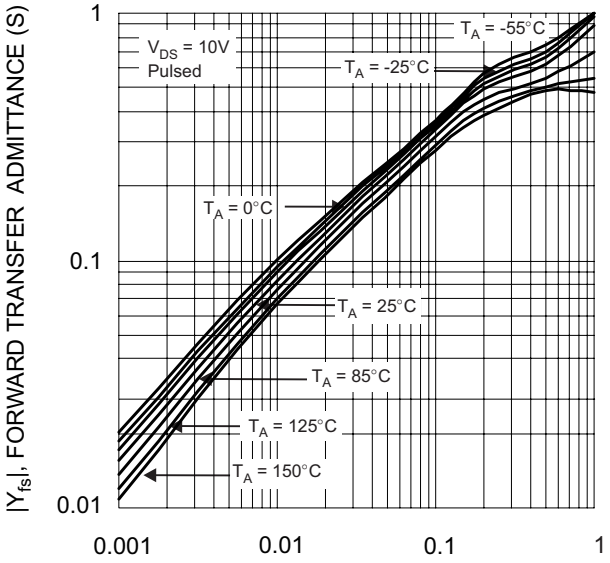


Fig.10 Forward Transfer Admittance vs. Drain Current

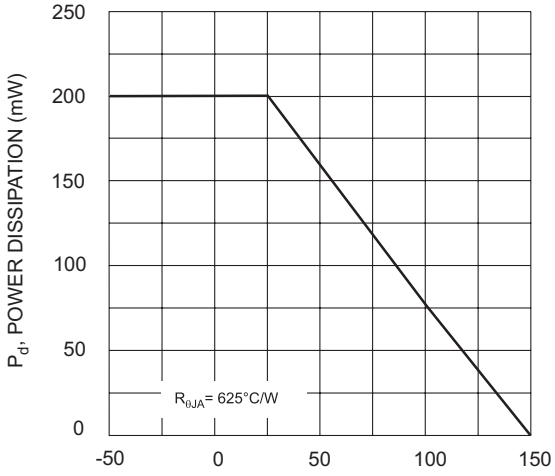


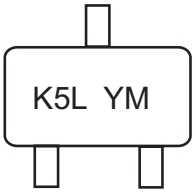
Fig. 11, Derating Curve - Total

Ordering Information (Note 5)

Device	Packaging	Shipping
DMN5L06W-7	SOT-323	3000/Tape & Reel

Notes: 4. Short duration test pulse used to minimize self-heating effect.
5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K5L = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: S = 2005
M = Month ex: 9 = September

Date Code Key

Year	2005	2006	2007	2008	2009
Code	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D